

NITRIDE ETCHSTOP FILM TO PROTECT METAL-INSULATOR- METAL CAPACITOR DIELECTRIC FROM DEGRADATION AND METHOD FOR MAKING SAME

Abstract of the Disclosure

A multilayer semiconductor device that includes a metal-insulator-metal (MIM) capacitor including a first metal plate, a dielectric layer, and a second metal plate, a nitride etchstop layer formed above the MIM capacitor, a first interlayer dielectric formed on the nitride etchstop layer, and a first via and a second via that extend through at least the first interlayer dielectric to contact the nitride etchstop layer.